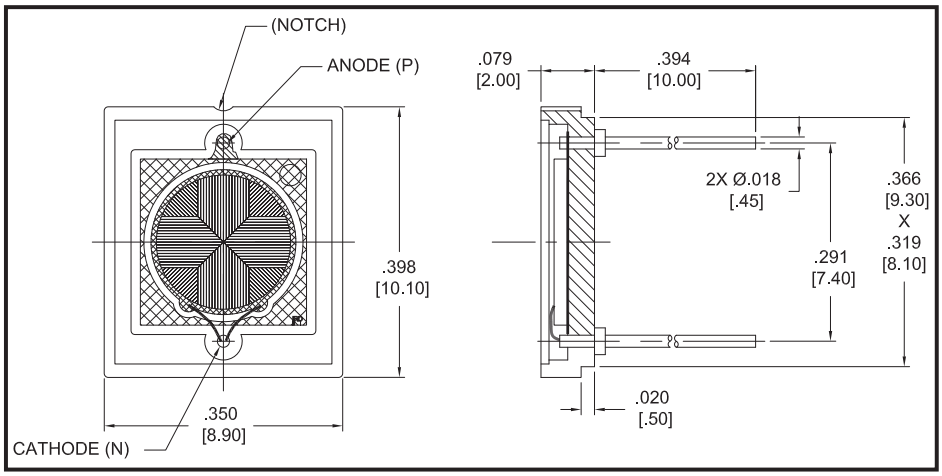


FEATURES

- Circular active area
- Ideal for EUV detection
- 100% internal QE
- High speed
- Grid lines 5 microns, Pitch 100 microns
- RoHS and REACH compliant

RoHS

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	Ø5.01mm		19.7		mm^2
Responsivity, $\mathcal{R}$	(see graphs on next page)				A/W
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$	160			Volts
Capacitance, C	$V_R = 0V$		200	800	pF
Rise Time	RL = 50Ω, V_R = 150V			2	nsec
Dark Current	V_R = 150V			100	nA

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient[1]	-10° TO 40°C[1]
Nitrogen or Vacuum	-20°C TO 80°C
Lead Soldering Temperature[2]	260°C

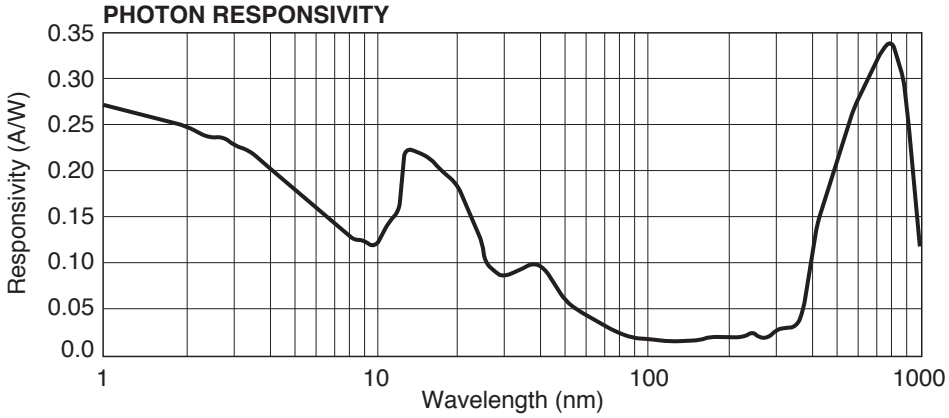
[1]Temperatures exceeding these parameters may create oxide growth on the active area.
Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

[2]0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

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